

Tutorial Questions #3:
Charge recombination; Doping; Open circuit; Fill factor;

1. Pn-junction

The p-type region of a silicon p-n junction is doped with 10^{16} boron atoms per cubic centimetre, and the n-type region is doped with 10^{18} phosphorus atoms per cubic centimetre. Assume a step p-n junction and that all doping atoms are ionized. The intrinsic carrier concentration in silicon at 300K is $1,5 \cdot 10^{10} \text{ cm}^{-3}$.

- a) What are the electron and hole concentrations in the p- and n-type regions at thermal equilibrium?
- b) Calculate the built-in voltage V_{bi} at 300K.
- c) Calculate the width of the depletion region at 300K

2. Open circuit voltage 1

A crystalline silicon solar cell generates a photocurrent density of $J_{ph} = 35 \frac{\text{mA}}{\text{cm}^2}$ at $T = 300\text{K}$. The saturation current density is $J_{ph} = 1,95 \cdot 10^{-10} \frac{\text{mA}}{\text{cm}^2}$. Assuming that the solar cell behaves as an ideal p-n junction, calculate the open circuit voltage V_{oc} .

3. Open circuit voltage 2

Which of the following statements is true?

- a) The open circuit voltage decreases when the lifetime of the minority charge carriers increases.
- b) The open circuit voltage increases when the irradiance increases.
- c) The open circuit voltage increases when the intrinsic density of charge carriers increases.
- d) The open circuit voltage does not depend on the doping.

4. Fill factor

John has used a solar simulator setup to measure the relationship between the voltage and the current of a small photovoltaic module (40cm long and 40cm wide). The measurement setup maintains the standard measurement conditions: the temperature is controlled to 25°C , the incident spectrum is the AM1.5 spectrum with an incident power density of $1000 \frac{\text{W}}{\text{m}^2}$. The result is illustrated in Figure 1. John determined that the maximum power he could get out of this module is $19,5\text{W}$.

- Determine the short-circuit current density.
- Calculate the fill factor of the module.
- What is the efficiency of the module?
- John decides to connect two of these modules with a cable in series. This results in an additional $2\text{m}\Omega$ series resistance loss. What is the new fill factor? (Hint: use the voltage drop at the maximum power point)

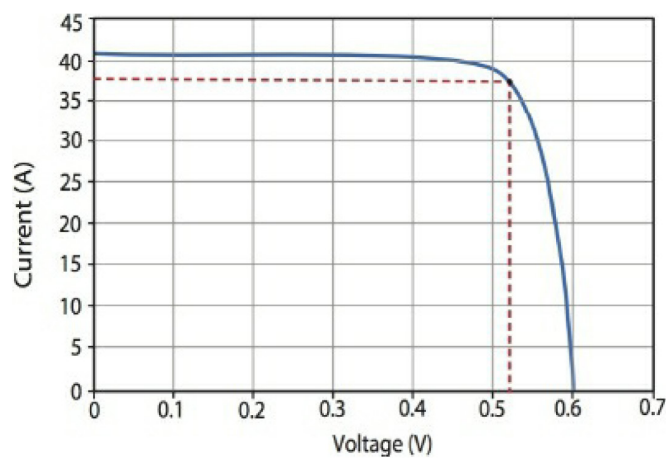


Figure 1